



## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	30V
$I_D$	1.1A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	450m
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	550m
$R_{DS(ON)}$ ( at $V_{GS}=2.5V$ )	850m

### General Description

Trench Power LV MOSFET technology  
Excellent package for heat dissipation  
High density cell design for low  $R_{DS(ON)}$   
Moisture Sensitivity Level 1  
Epoxy Meets UL 94 V-0 Flammability Rating  
Halogen Free

### Applications

Power switching application  
Uninterruptible power supply  
DC-DC convertor

**Absolute Maximum Ratings** ( $T_A=25^\circ C$  unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	30	V
Gate-source Voltage	$V_{GS}$	$\pm 12$	V

Trent Tf1 0 0 1 344.35 434.1W\* nq

Drain Current

**Electrical Characteristics (T<sub>J</sub>=25 °C unless otherwise noted)**

Parameter	Symbol	

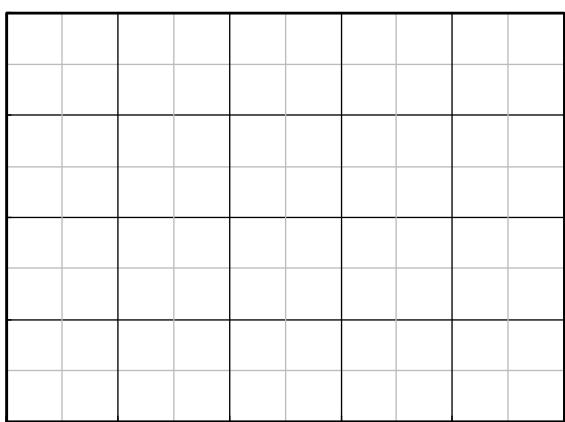
**Typical Electrical and Thermal Characteristics Diagrams**

Figure 1. Output Characteristics

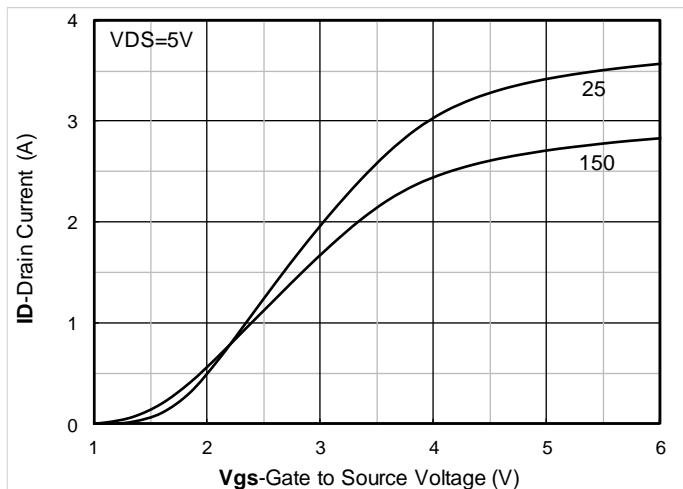


Figure 2. Transfer Characteristics

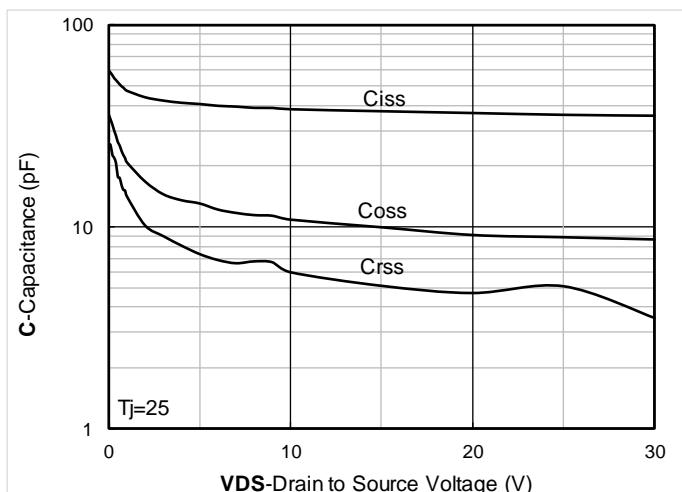


Figure 3. Capacitance Characteristics

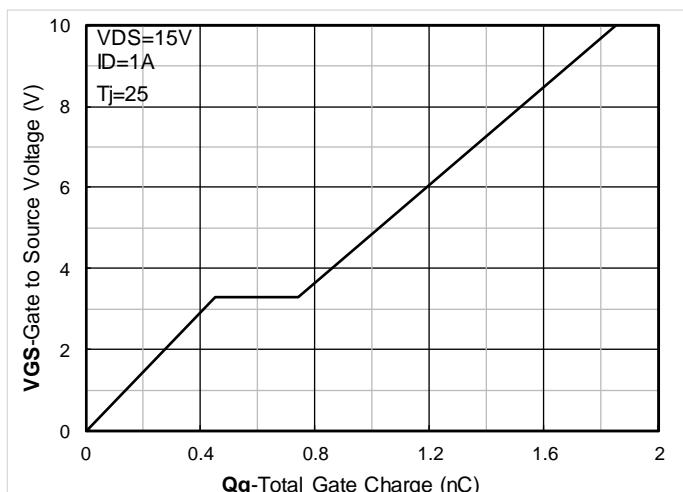


Figure 4. Gate Charge

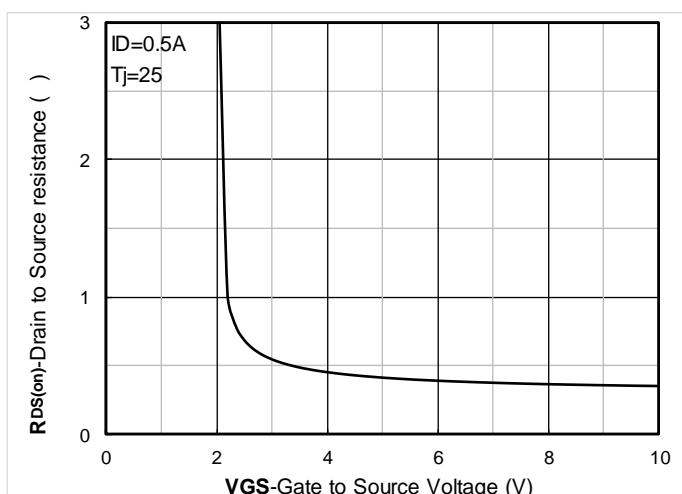


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance

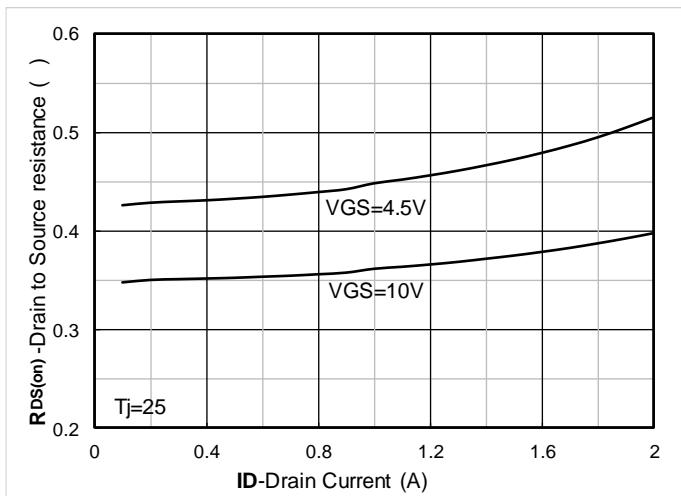


Figure 7. RDS(on) VS Drain Current

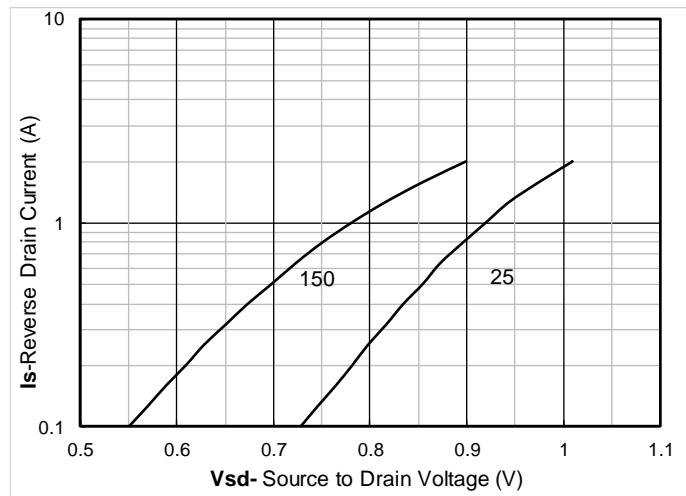


Figure 8. Forward characteristics of reverse diode

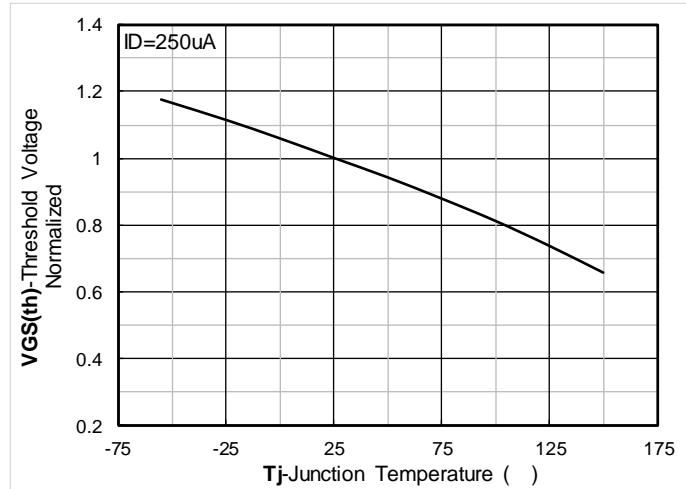


Figure 9. Normalized breakdown voltage

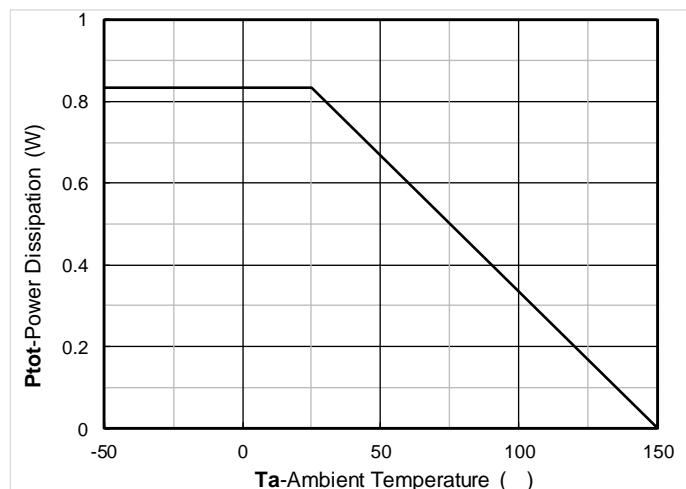


Figure 10. Normalized Threshold voltage

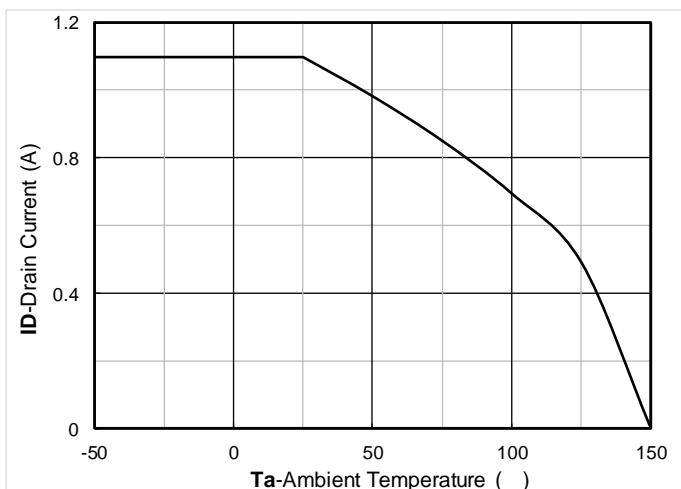


Figure 11. Current dissipation

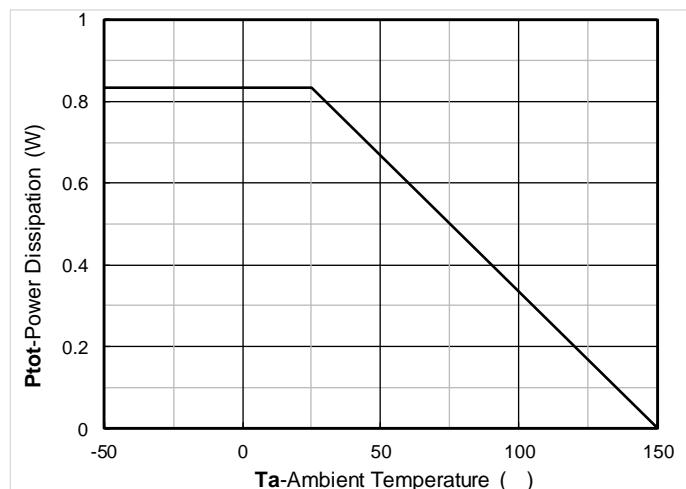


Figure 12. Power dissipation

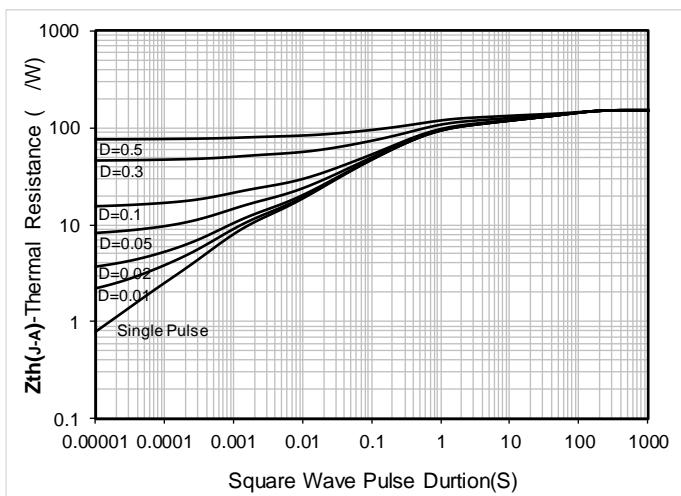


Figure 13. Maximum Transient Thermal Impedance

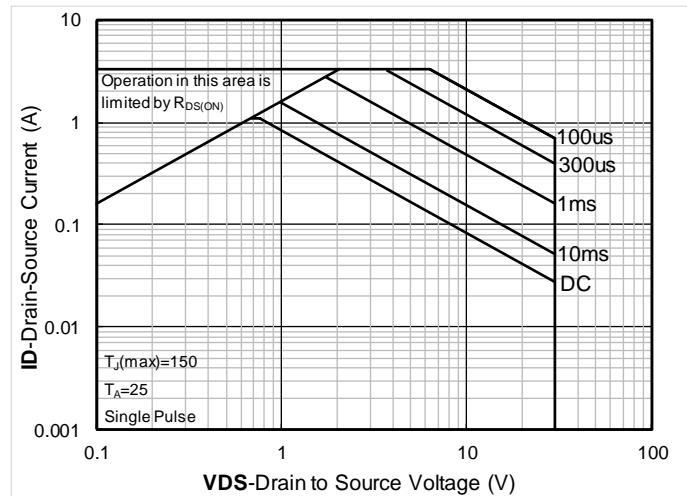


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

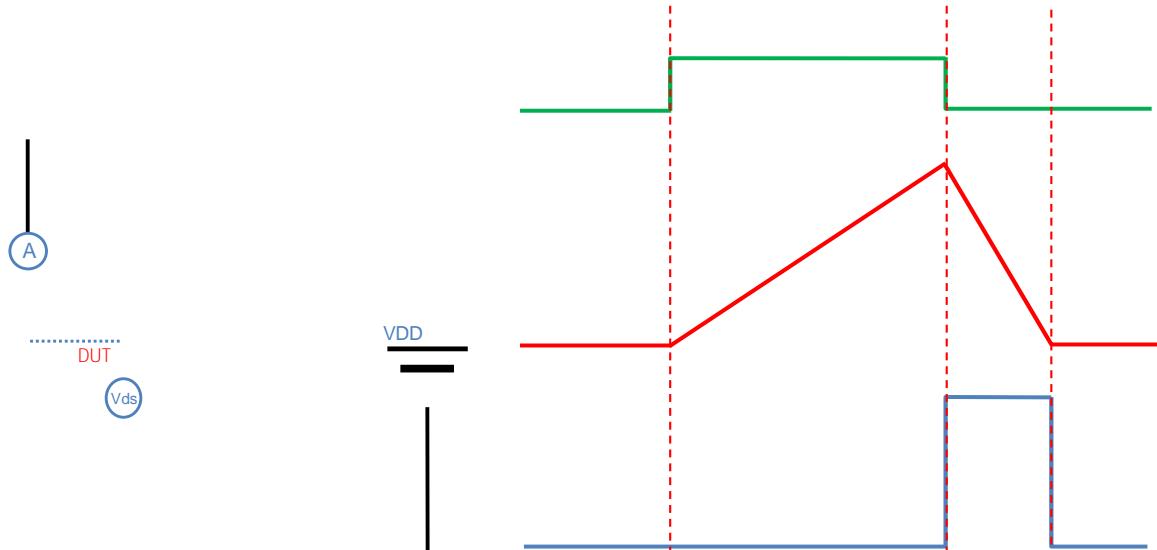


Figure A. Unclamped Inductive Switching (UIS) Test Circuit &amp; Waveform

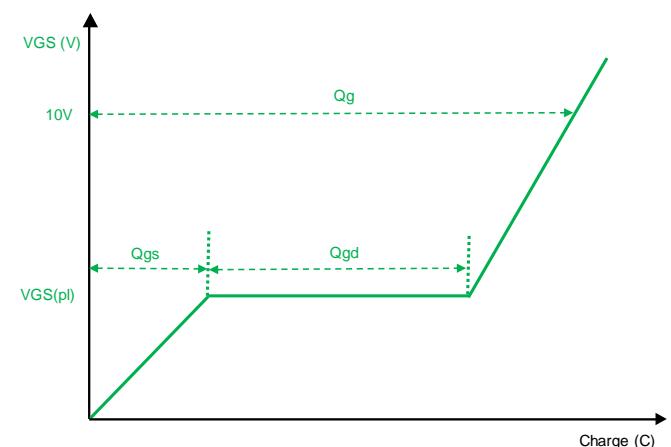
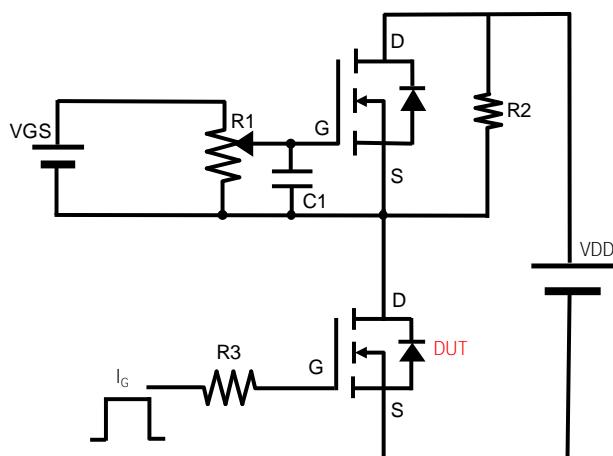


Figure B. Gate Charge Test Circuit & Waveform

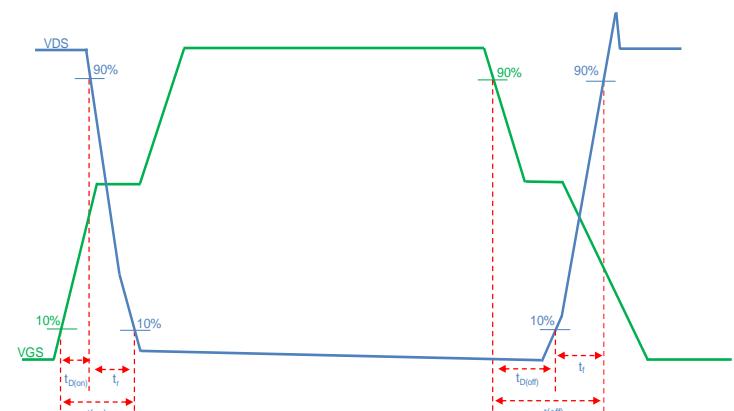
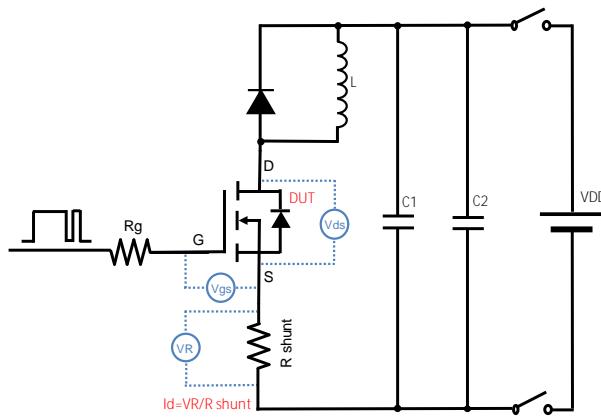


Figure C. Resistive Switching Test Circuit & Waveform

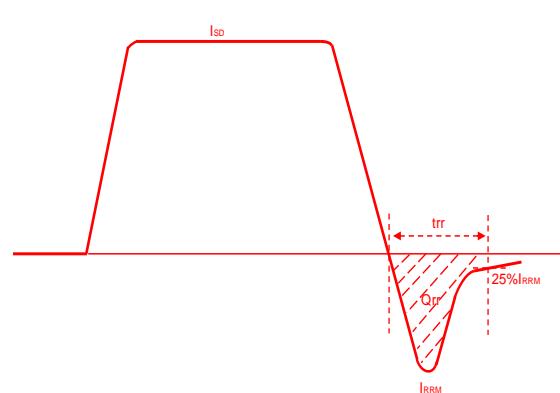
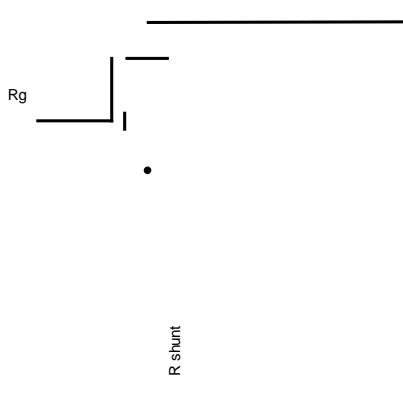
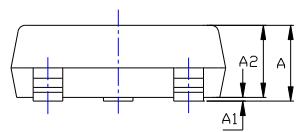
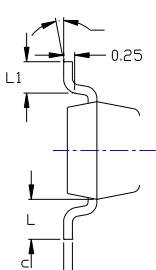
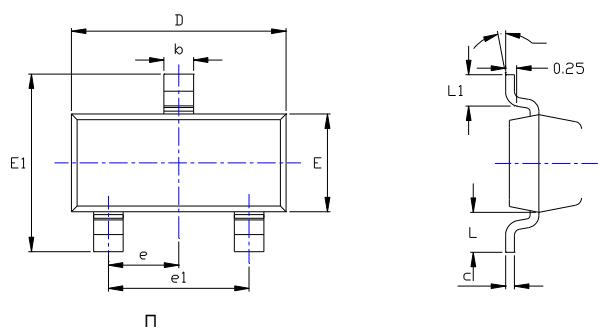


Figure D. Diode Recovery Test Circuit & Waveform



## SOT-23 Package information



UNIT mm





## Disclaimer

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